

Silicon NPN Power Transistors

S2000

DESCRIPTION

- With TO-3PH package
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- Color TV horizontal output applications
- Color TV switching regulator applications

PINNING(See Fig.2).

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

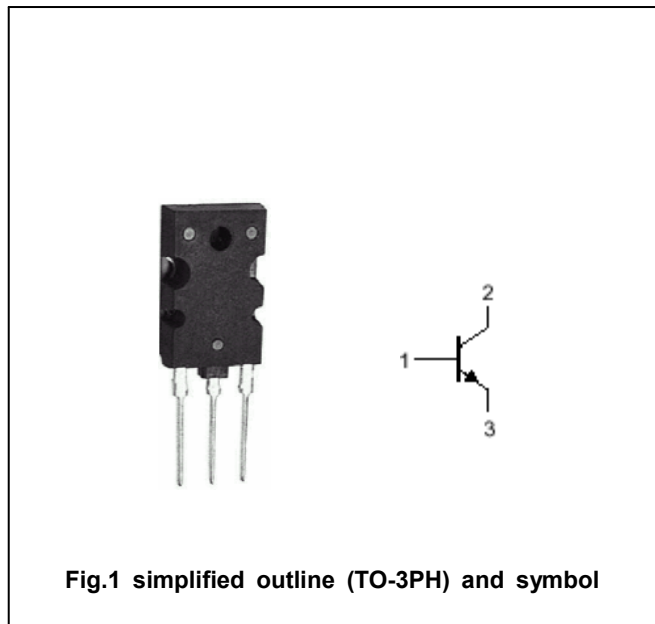


Fig.1 simplified outline (TO-3PH) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		15	A
I _B	Base current		4	A
P _C	Collector power dissipation	T _C =25 °C	125	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _B =500mA ; V _{BE} =-1.7V; L=40mH	700			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =1.0A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =4.5A ; I _B =1.0A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =1500V; V _{BE} =0			1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	10		30	
h _{FE-2}	DC current gain	I _C =4.5A ; V _{CE} =5V	4.5		9	
C _{OB}	Collector output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		95		pF
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		2		MHz

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PACKAGE OUTLINE

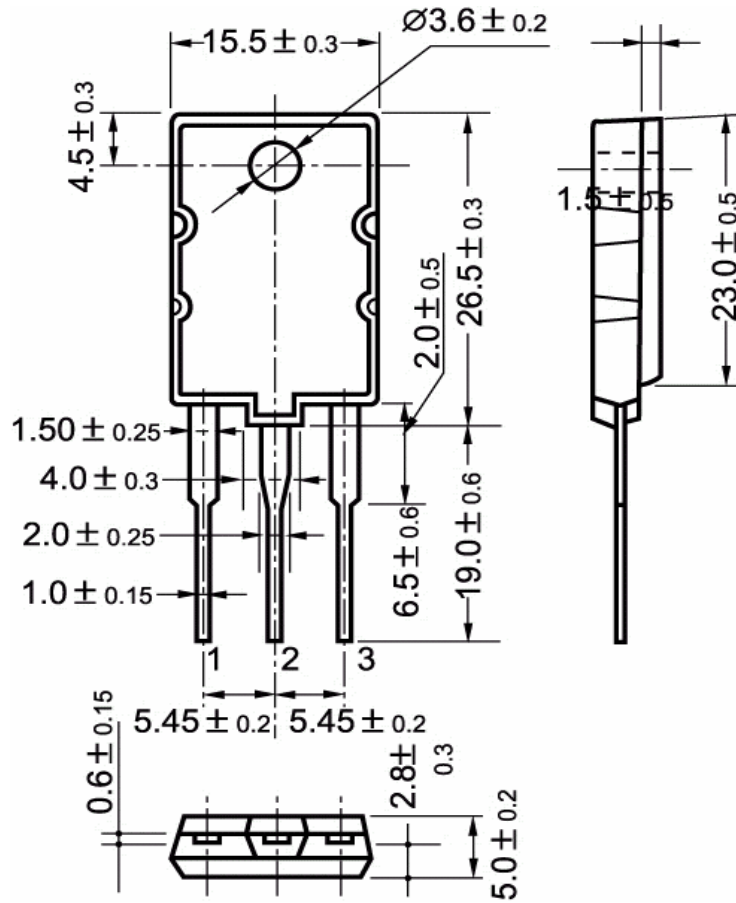


Fig.2 outline dimensions